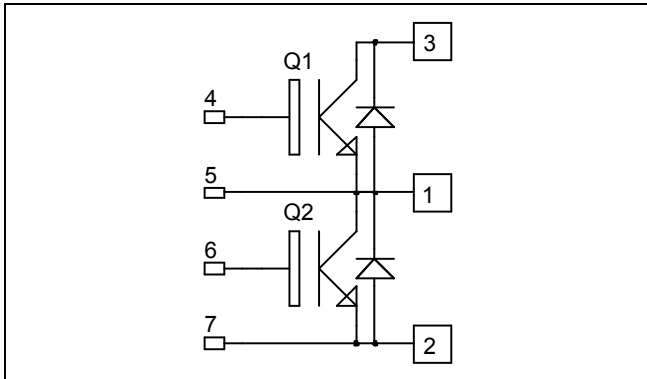


*Phase leg  
Trench + Field Stop IGBT3  
Power Module*

**$V_{CES} = 600V$   
 $I_C = 300A @ T_c = 80^\circ C$**



### Application

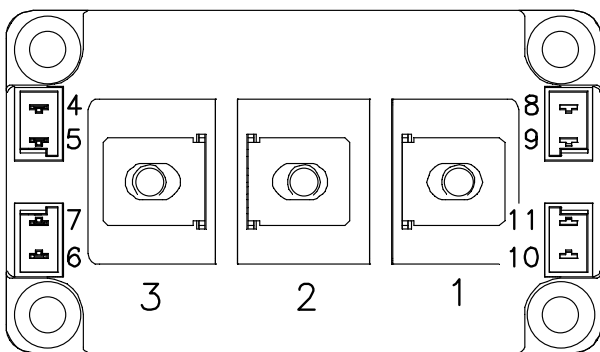
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant



### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	400
		$T_C = 80^\circ C$	300
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	600
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	940
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	600A @ 520V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			500	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 300A$		$T_j = 25^\circ\text{C}$ 1.5 $T_j = 150^\circ\text{C}$ 1.7	1.9	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4.8\text{ mA}$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		18.5		nF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		1.2		
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.5		
$Q_G$	Gate charge	$V_{GE} = \pm 15V, I_C = 300A$ $V_{CE} = 300V$		3.2		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 300A$ $R_G = 2.2\Omega$		110		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			490		
$T_f$	Fall Time			50		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 300A$ $R_G = 2.2\Omega$		130		ns
$T_r$	Rise Time			60		
$T_{d(off)}$	Turn-off Delay Time			530		
$T_f$	Fall Time			70		
$E_{on}$	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 25^\circ\text{C}$	3.1		mJ
$E_{off}$	Turn off Energy	$I_C = 300A$ $R_G = 2.2\Omega$	$T_j = 150^\circ\text{C}$	3.3		
			$T_j = 25^\circ\text{C}$	12		
			$T_j = 150^\circ\text{C}$	12.5		
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 360V$ $t_p \leq 6\mu\text{s}; T_j = 150^\circ\text{C}$		1500		A

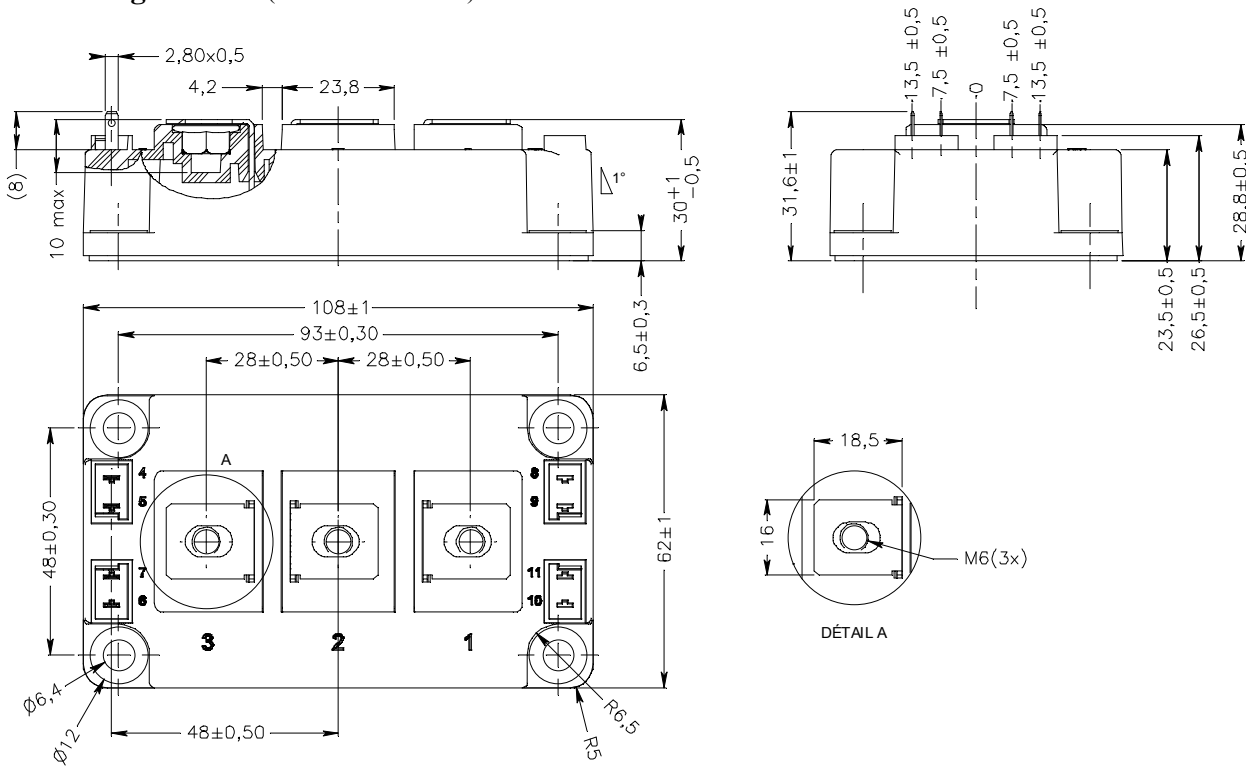
**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RRM}$	Maximum Reverse Leakage Current	$V_R = 600V$			$T_j = 25^\circ\text{C}$ 500 $T_j = 150^\circ\text{C}$ 750	$\mu\text{A}$
$I_F$	DC Forward Current			300		A
$V_F$	Diode Forward Voltage	$I_F = 300A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$	1.6	2	V
			$T_j = 150^\circ\text{C}$	1.5		
$t_{rr}$	Reverse Recovery Time	$I_F = 300A$ $V_R = 300V$ $di/dt = 4800A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	100		ns
			$T_j = 150^\circ\text{C}$	150		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 300A$ $V_R = 300V$ $di/dt = 4800A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	14.4		$\mu\text{C}$
			$T_j = 150^\circ\text{C}$	30.4		
$E_{rr}$	Reverse Recovery Energy	$I_F = 300A$ $V_R = 300V$ $di/dt = 4800A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	3.4		mJ
			$T_j = 150^\circ\text{C}$	7.2		

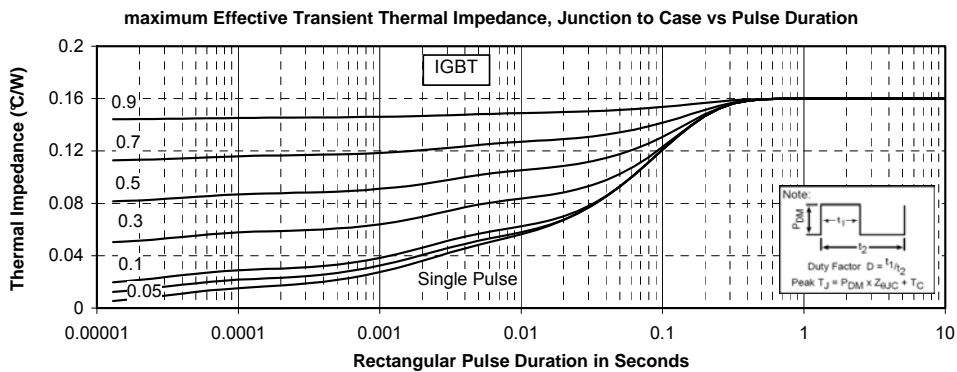
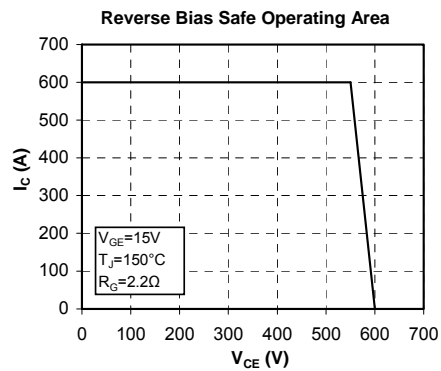
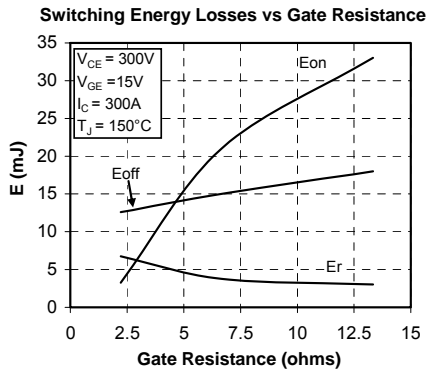
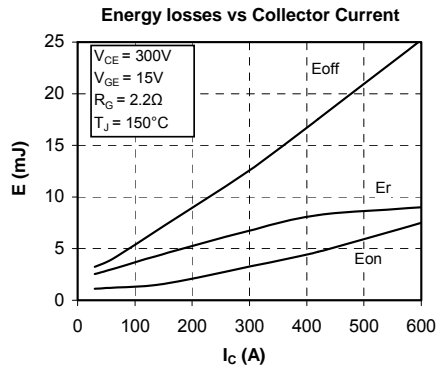
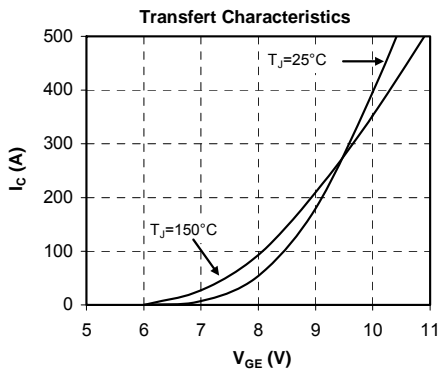
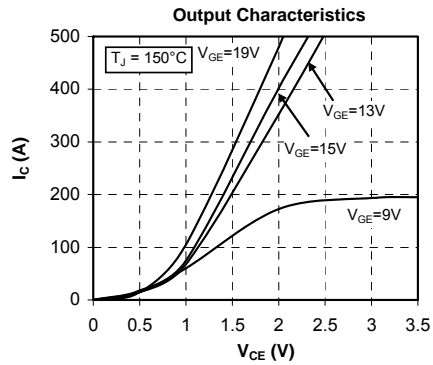
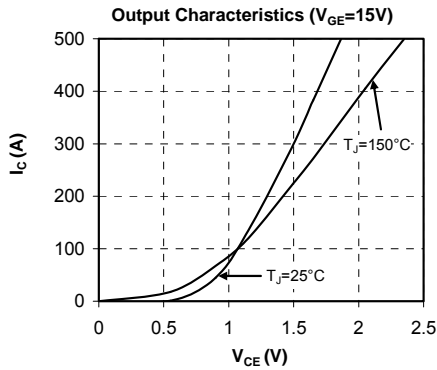
## Thermal and package characteristics

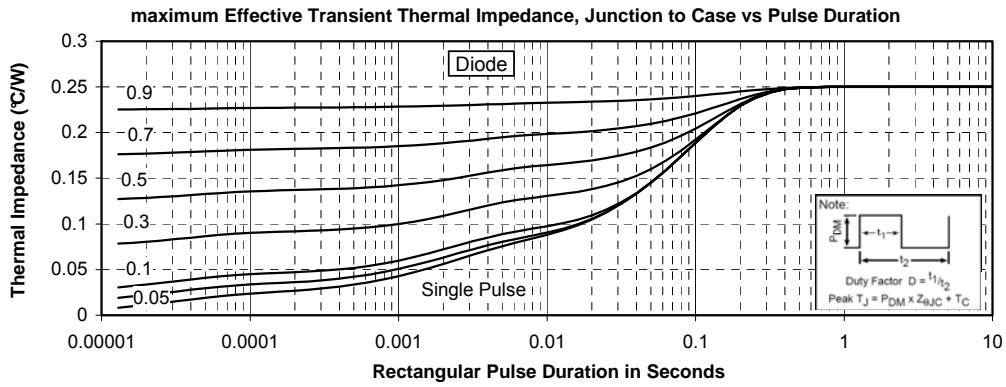
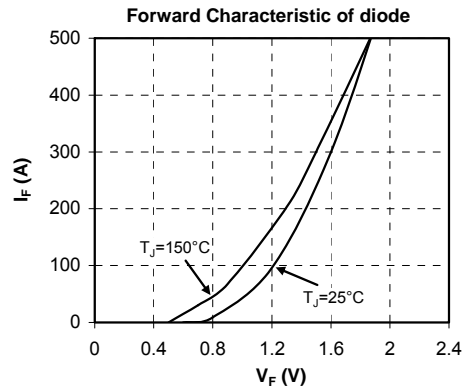
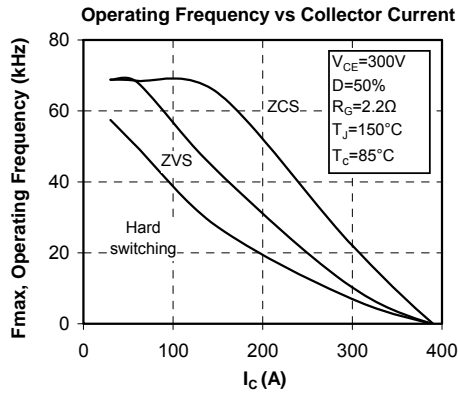
Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.16	°C/W	
		Diode		0.25		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	-40		175	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals	M6	3	5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight			350	g	

### D3 Package outline (dimensions in mm)



## Typical Performance Curve





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